

**ECE 692/599**

# Fundamentals of Semiconductors: Physics and Materials Properties



A SEMI-CONDUCTOR

Taken from Yu & Cardona, Fundamentals of Semiconductors: Physics and Materials Properties

Gong Gu

Spring 2020

## Purposes

- To prepare **EE students** in electronic materials and devices related research areas with adequate background knowledge in semiconductor physics and processing;
- To bridge the gap between frontier research in condensed matter physics and real-world applications in the semiconductor industry for **Physics and Chemistry students**; and
- To relate advanced materials research, including materials preparation and characterization techniques, to micro- and nanoelectronics for **MSE students**.

**Selected advance topics** (TBD by student research areas and interests:  
e.g. wide-band gap semiconductors for power electronics, defect engineering for memristors, first-principles methods for computational materials science or condensed matter physics, etc.)

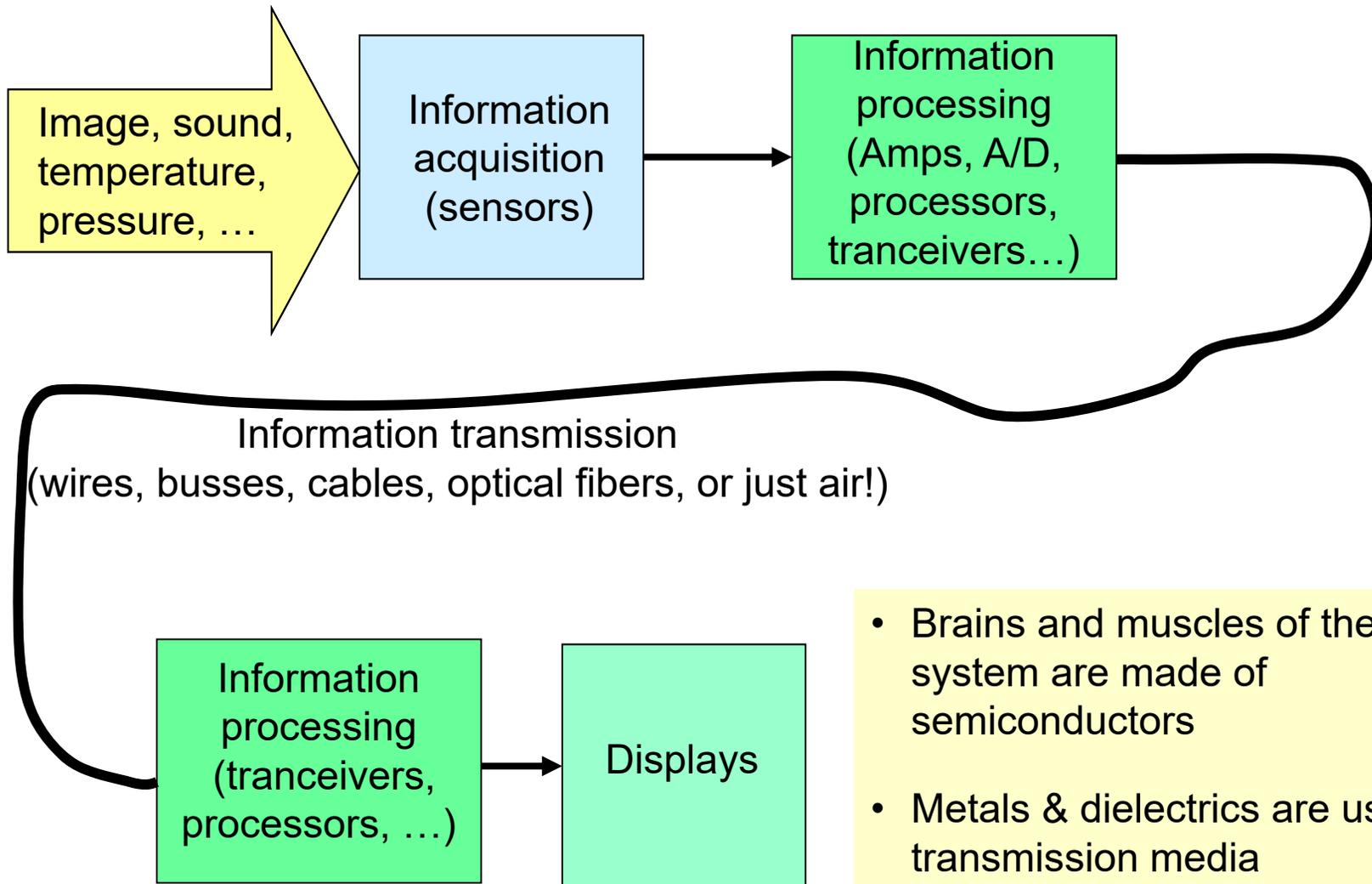
So, let's know each other.

### **Student background survey**

Name, major, research field, advisor

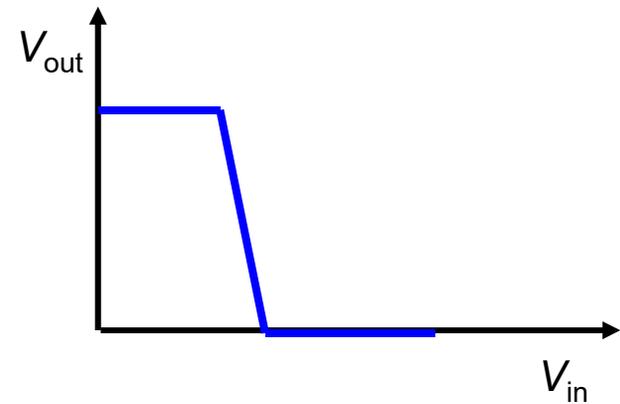
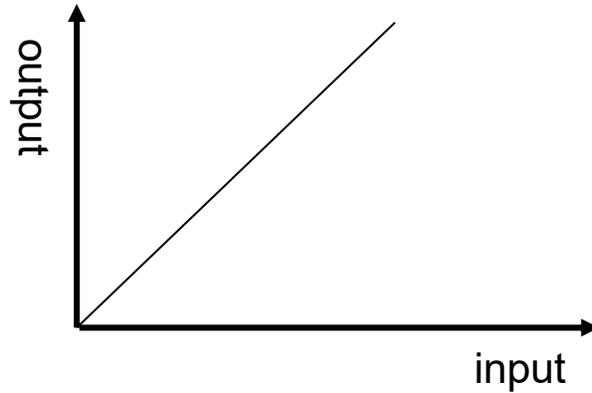
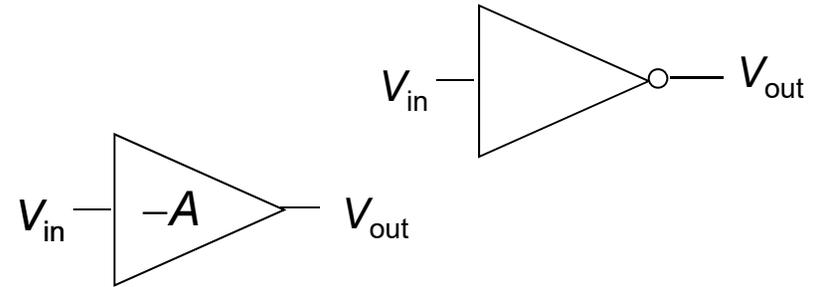
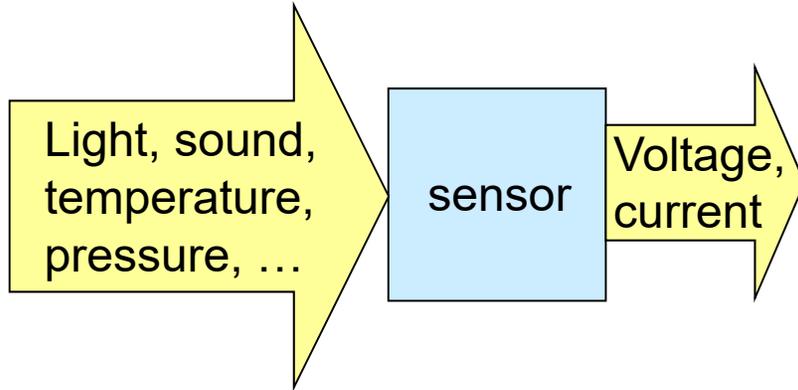
# Why Semiconductors?

Sometimes we say “solid state”



- Brains and muscles of the system are made of semiconductors
- Metals & dielectrics are used as transmission media
- Why?

What's common for all the core components?

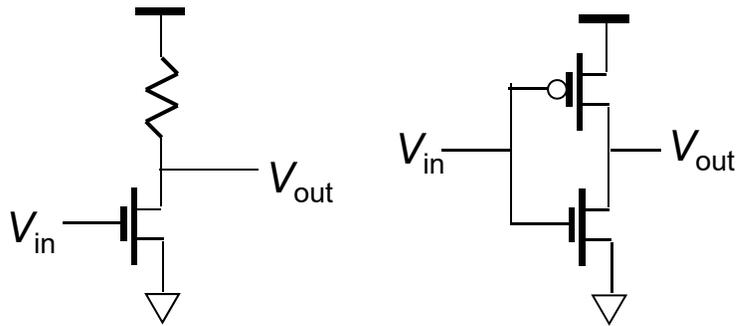


Modulation of some physical quantity (output) by some others

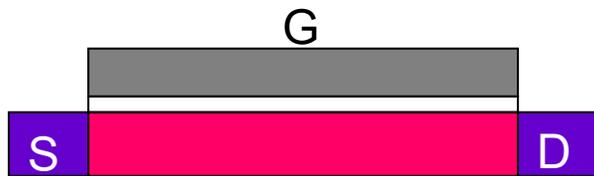
Some kind of gain, conversion ratio, sensitivity, etc

# Example: Field-Effect Transistors (FETs)

## Semiconductor vs Metal



FET's are building blocks.



Schematic illustration of a FET

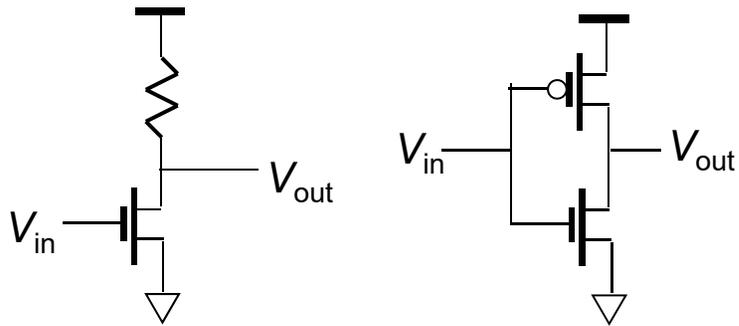
For  $\text{SiO}_2$  dielectric, breakdown field  $E_b \sim 10^7$  V/cm.  
 No matter how thick it is, the maximum induced carrier area density is  $\epsilon_r \epsilon_0 E_b / q = 2 \times 10^{13}$  /cm<sup>2</sup>.  
 (Recall Gauss's law)

For a 1  $\mu\text{m}$  thick Si channel, the intrinsic carrier density  $n_i = 1.45 \times 10^{10}$  /cm<sup>3</sup>,  
 the background carrier area density is  $n_i \times 10^{-4}$  cm =  $1.45 \times 10^6$  /cm<sup>2</sup>. ( $\times 2$ , considering both electrons and holes)

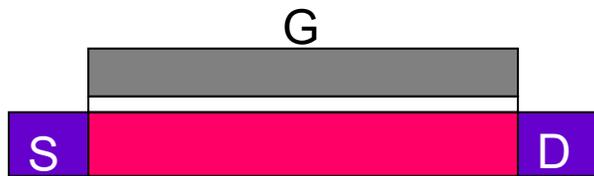
In principle, the area carrier density, and therefore the channel conductance, can be modulated by 7 orders of mag!!!

# Example: Field-Effect Transistors (FETs)

## Semiconductor vs Metal



FET's are building blocks.



Schematic illustration of a FET

For SiO<sub>2</sub> dielectric, breakdown field  $E_b \sim 10^7$  V/cm.  
No matter how thick it is, the maximum induced carrier area density is  $\epsilon_r \epsilon_0 E_b / q = 2 \times 10^{13}$  /cm<sup>2</sup>.  
(Recall Gauss's law)

For a **1  $\mu\text{m}$  thick** Si channel,  
 $n_i = 1.45 \times 10^{10}$  /cm<sup>3</sup>,  
the background carrier area density is  
 $n_i \times 10^{-4}$  cm =  $1.45 \times 10^6$  /cm<sup>2</sup>.

In principle, the area carrier density, and therefore the channel conductance, can be modulated by 7 orders of mag!!!

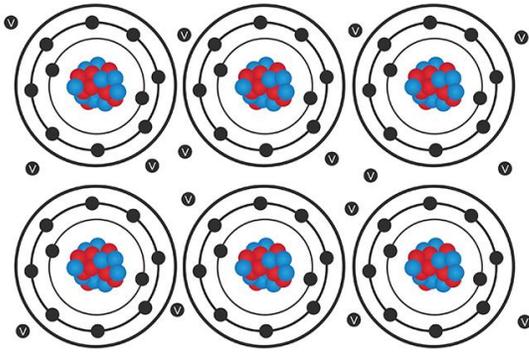
(Si's next-door neighbor in the periodic table)

For Al,  $n = 1.8 \times 10^{23}$  /cm<sup>3</sup>. Even for **1 nm thin (monolayers!) Al**, the background carrier area density is  $1.8 \times 10^{16}$  /cm<sup>2</sup>. The conductance can only be modulated by 0.1%!!!

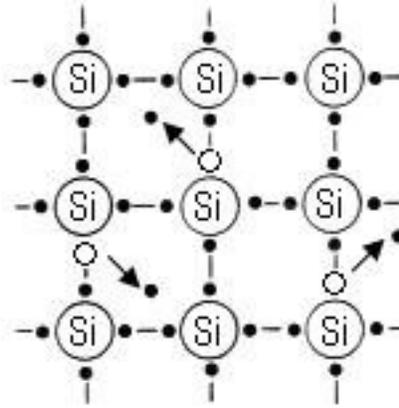
What makes this difference?

# What are semiconductors??? -- Simplified pictures

Bond picture

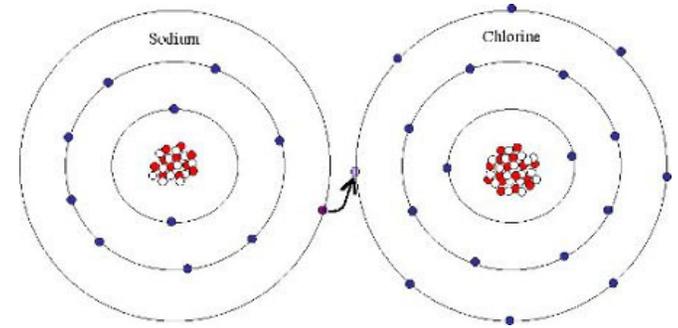


<https://infogr.am/how-does-bond-structure-affect-melting-point>



<https://keterehsky.wordpress.com/2010/03/10/9-2-semiconductor-diod/>

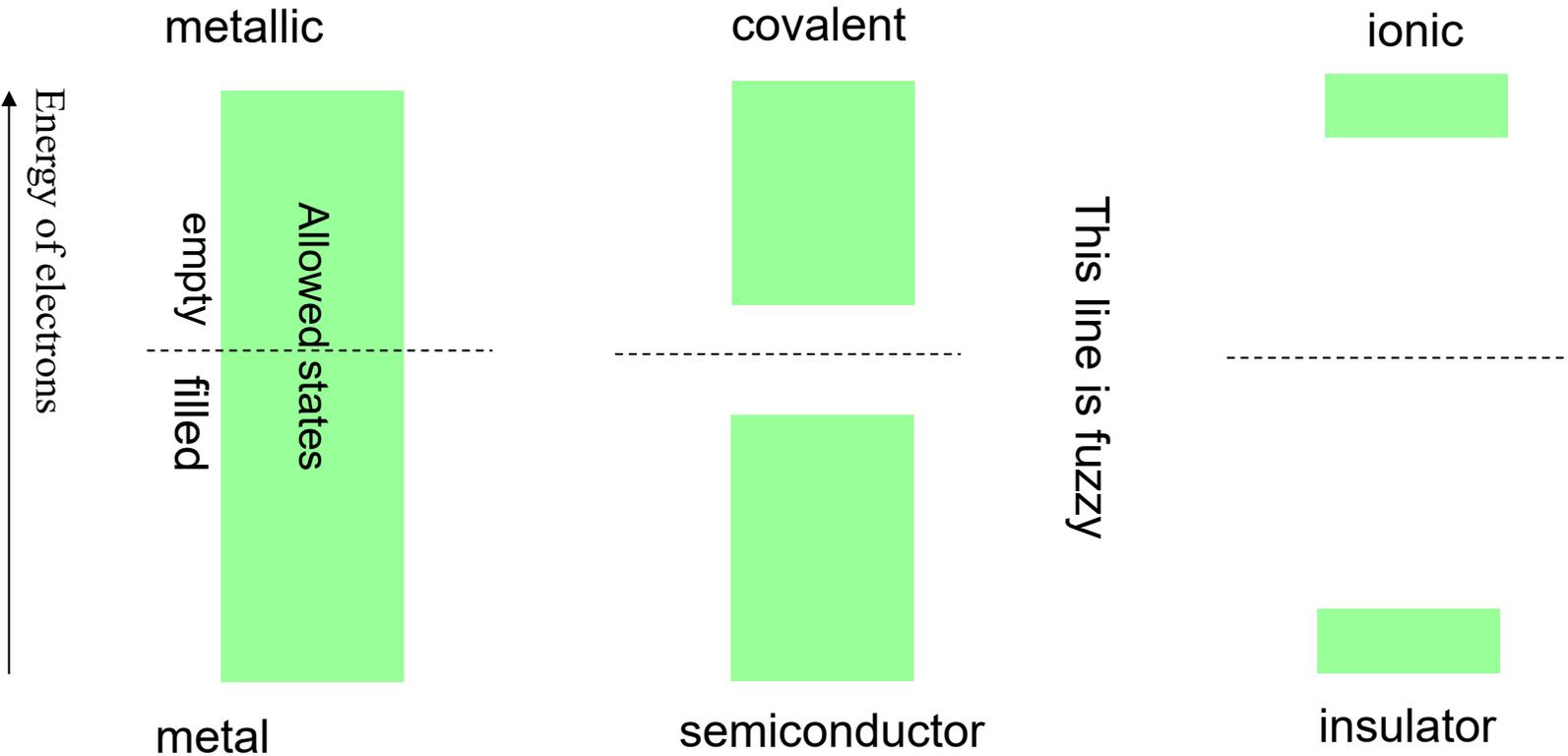
NaCl



<http://knowledgebase.lookseek.com/Chemistry-Bonds-Ionic-Bonding.html>

Metal: "electron gas"

Band picture



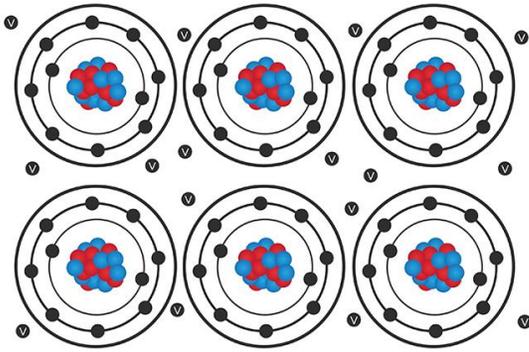
metal

semiconductor

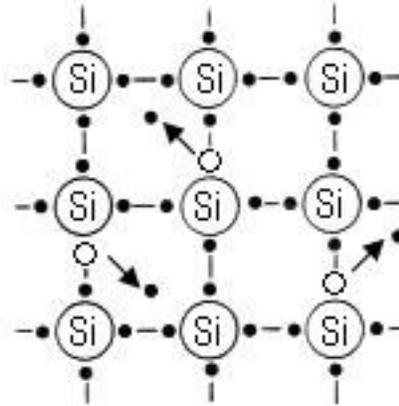
insulator

# What are semiconductors??? -- Simplified pictures

Bond picture

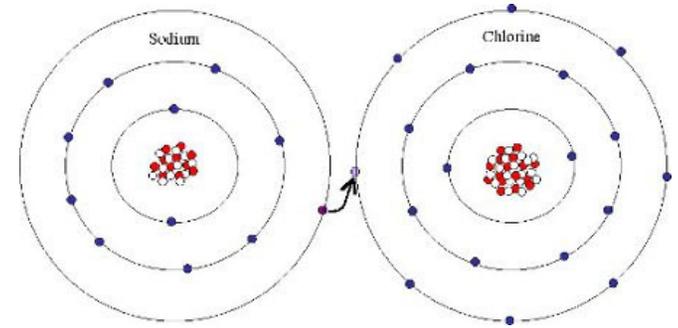


<https://infogr.am/how-does-bond-structure-affect-melting-point>



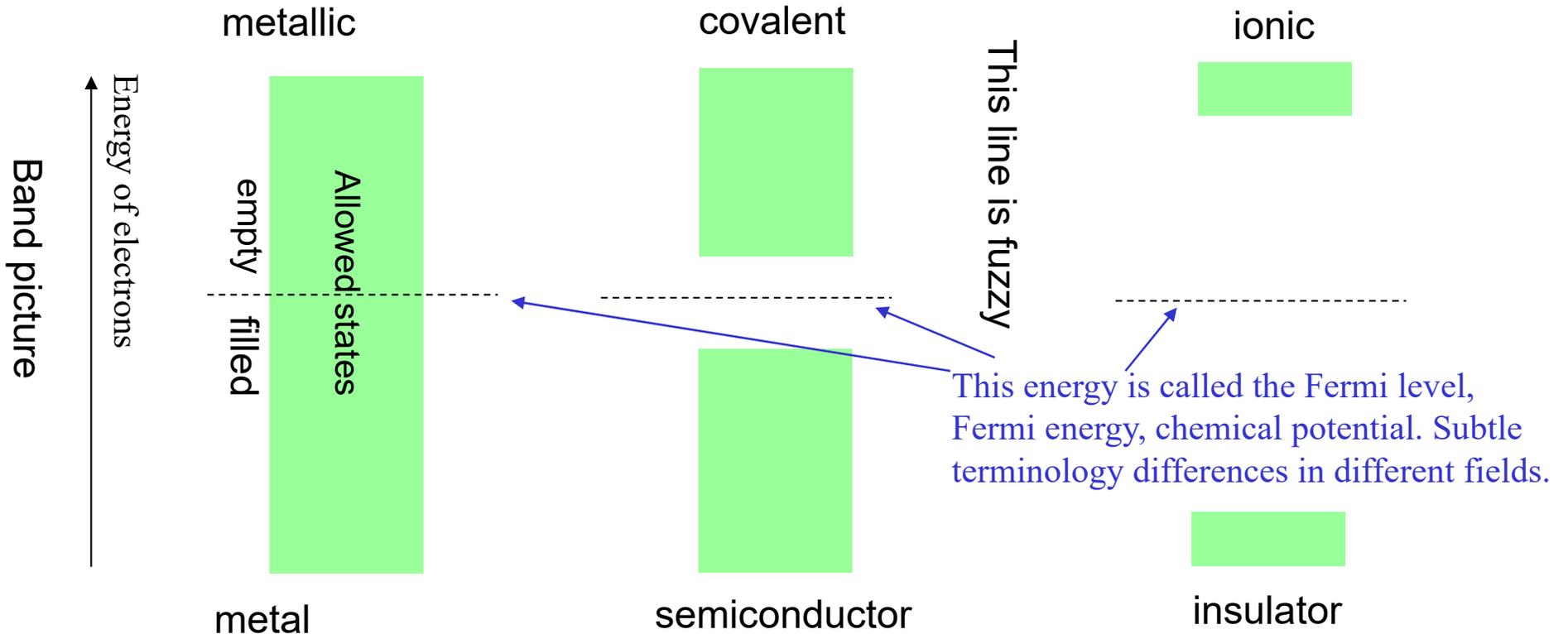
<https://keterehsky.wordpress.com/2010/03/10/9-2-semiconductor-diod/>

NaCl



<http://knowledgebase.lookseek.com/Chemistry-Bonds-Ionic-Bonding.html>

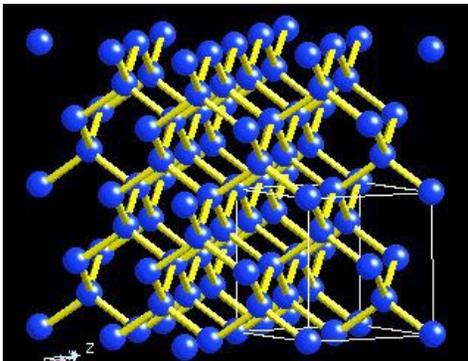
Metal: "electron gas"



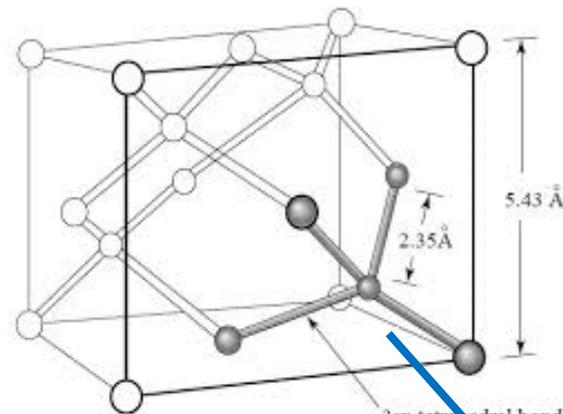
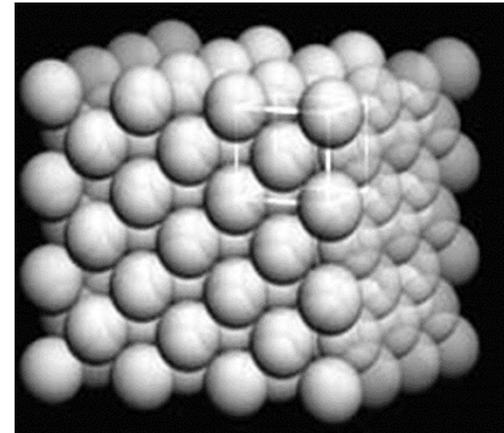
# What are semiconductors, anyway???

Si:  $Z = 14$ ,  $1s^2 2s^2 2p^6 3s^2 3p^2$ , group IV

Al:  $Z = 13$ ,  $1s^2 2s^2 2p^6 3s^2 3p^1$ , group III

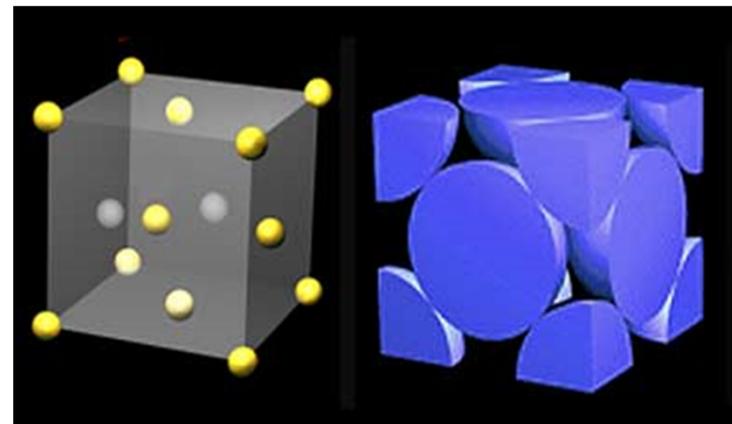


[http://www.webelements.com/silicon/crystal\\_structure.html](http://www.webelements.com/silicon/crystal_structure.html)

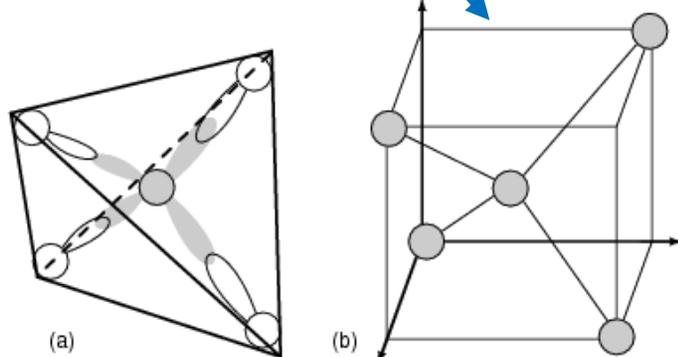


$sp^3$  hybridization

<http://onlineheavytheory.net/silicon.html>



[https://www.nde-ed.org/EducationResources/CommunityCollege/Materials/Structure/metallic\\_structures.htm](https://www.nde-ed.org/EducationResources/CommunityCollege/Materials/Structure/metallic_structures.htm)



[http://www.learningelectronics.net/vol\\_3/chpt\\_2/3.html](http://www.learningelectronics.net/vol_3/chpt_2/3.html)

To really understand the bond and band pictures of semiconductors (actually all solids), we must start from quantum mechanics.

But we will first review some commonly used concepts.

A common concept that often falls through the gap (between courses)

## What is voltage?

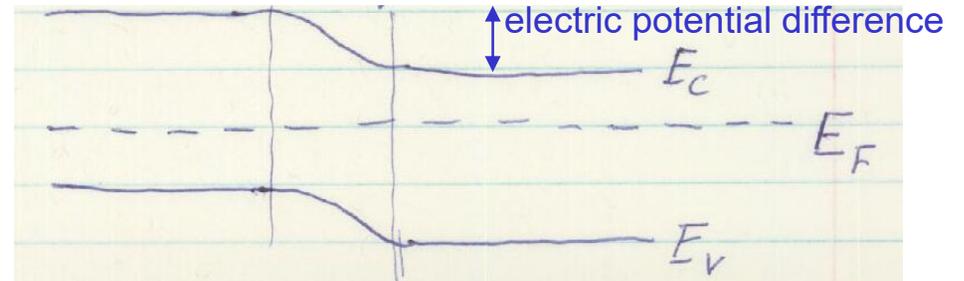
In electromagnetism, we were taught that the voltage is an electric potential difference.

Later, we studied semiconductor devices.

Here's what we were told:

The pn junction has a built-in "voltage" that you cannot measure with a voltmeter.

If you try, the meter reads zero.

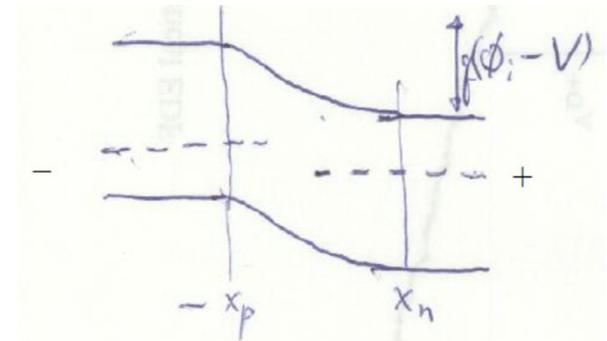


The built-in voltage, however, **is** an electrostatic potential difference.

Then we moved on to study the pn junction under bias.

Here's what we were told:

The voltage (applied voltage to the pn junction in a circuit) is the difference between the two Fermi levels.



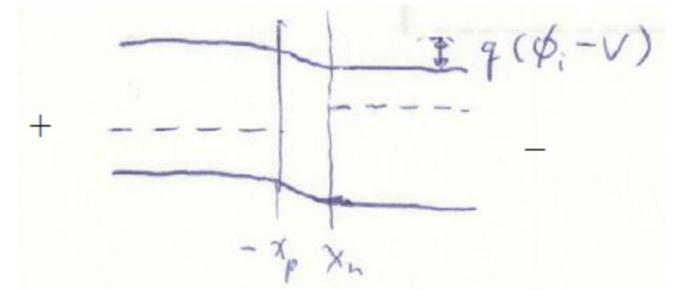
What's going on? What is voltage, after all?

Let's do some Gedankenexperiments:

A charged capacitor, a battery.

Measure the voltage with a voltmeter.

Drive a load...



## Summary & Outlook

- Semiconductors are used in active devices in information systems because they provide large **modulation** ranges.
- This is due to their properties derived from their chemical compositions and structures.
- We view solid-state materials from two complementary and unified perspectives: the **bond** picture and the **band** picture.
- The band picture is powerful in understanding the electrical and optical properties of semiconductors:
  - Conduction band, valence band, and the gap...
  - States are occupied by electrons up to the “**Fermi level**” (at zero temperature; there is a distribution at nonzero temperatures). Keep in mind terminology difference between fields.
  - We can thank the **band gap** for the large modulation range.
- The bond picture helps us appreciate structures, understand things like surface, interfaces, defects (increasing important in this age of nanoelectronics)
- The two pictures are unified.
- To really understand all these topics, we need quantum mechanics...
- Before we move on to quantum mechanics and solid-state physics based thereon, we will first review common concepts in semiconductor device physics, and **ask questions**.
- First, we re-discovered the **voltage**.